

AMENDMENTS

Please amend the above-identified application as follows:

In The Specification

In accordance with 37 C.F.R. § 1.121, please substitute the following clean copy text for the following paragraph:

In the paragraph that spans page 1, lines 7-16:

~~This application is a division of U.S. Application Serial No. 08/932,025, entitled 'Method And Apparatus For Low Energy Electron Enhanced Etching of Substrates in an AC or DC Plasma Environment, filed September 17, 1997, which claims priority to and the benefit of the filing date of Provisional Patent Application Serial Nos. 60/026,985, filed September 20, 1996, entitled "APPARATUS AND PROCESS FOR LOW-DAMAGE DRY ETCHING OF INSULATOR BY LOW ENERGY ELECTRON ENHANCED ETCHING IN A DC PLASMA"; 60/026,587, filed September 20, 1996, entitled "APPARATUS AND PROCESS FOR LOW-DAMAGE DRY ETCHING OF INSULATOR BY LOW ENERGY ELECTRON ENHANCED ETCHING IN AN AC PLASMA"; and U.S. Patent Application Serial No. 08/705,902, filed on August 28, 1996 entitled "METHOD AND APPARATUS FOR LOW ENERGY ELECTRON ENHANCED ETCHING OF SUBSTRATES".~~

In The Claims

In accordance with 37 C.F.R. § 1.121, please cancel claims 1-18.